

FEATURES

Complimentary to S8050

MARKING: 2TY

**S8550** (PNP)



MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-25	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current -Continuous	I <sub>C</sub>	-0.5	A
Collector Power Dissipation	P <sub>C</sub>	0.3	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V <sub>CBO</sub>	I <sub>C</sub> = -100μA, I <sub>E</sub> =0	-40		V
Collector-emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = -1mA, I <sub>B</sub> =0	-20		V
Emitter-base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = -100μA, I <sub>C</sub> =0	-5		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -40V, I <sub>E</sub> =0		-0.1	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> = -20V, I <sub>B</sub> =0		-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -3V, I <sub>C</sub> =0		-0.1	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> = -1V, I <sub>C</sub> = -50mA	120	400	
	h <sub>FE(2)</sub>	V <sub>CE</sub> = -1V, I <sub>C</sub> = -500mA	5		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-500mA, I <sub>B</sub> = -50mA		-0.6	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-500mA, I <sub>B</sub> = -50mA		-1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -6V, I <sub>C</sub> = -20mA f=30MHz	150		MHz

CLASSIFICATION OF h<sub>FE</sub>

Rank	L	H	
Range	120-200	200-350	

S8550 Typical Characteristics

